

1S2074 (H)

Silicon Epitaxial Planar Diode for High Speed Switching

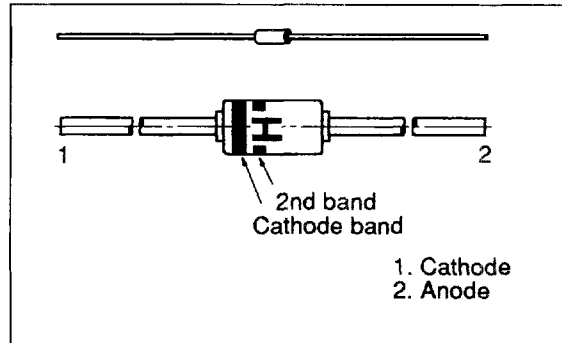
Features

- Low capacitance. ($C=3.0\text{pF}$ max)
- Short reverse recovery time. ($t_{rr}=4.0\text{ns}$ max)
- High reliability with glass seal.

Ordering Information

Type No.	Cathode	2nd band	Mark	Package Code
1S2074(H)	Green	White	H	DO-35

Outline



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

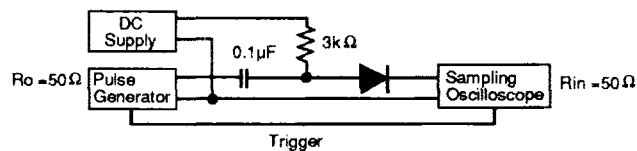
Item	Symbol	Value	Unit
Peak reverse voltage	V_{RM}	50	V
Reverse voltage	V_R	45	V
Peak forward current	I_{FM}	450	mA
Non-Repetitive peak forward surge current	I_{FSM}^*	600	mA
Average forward current	I_o	150	mA
Power dissipation	P_d	250	mW
Junction temperature	T_j	175	$^\circ\text{C}$
Storage temperature	T_{stg}	-65 to +175	$^\circ\text{C}$

* Within 1s forward surge current.

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	0.64	—	0.8	V	$I_F = 10\text{ mA}$
Reverse current	I_R	—	—	0.1	μA	$V_R = 30\text{ V}$
Capacitance	C	—	—	3.0	pF	$V_R = 1\text{ V}, f = 1\text{ MHz}$
Reverse recovery time	t_{rr}^*	—	—	4.0	ns	$I_F = I_R = 10\text{ mA}, I_{rr} = 1\text{ mA}$

* Reverse recovery time test circuit



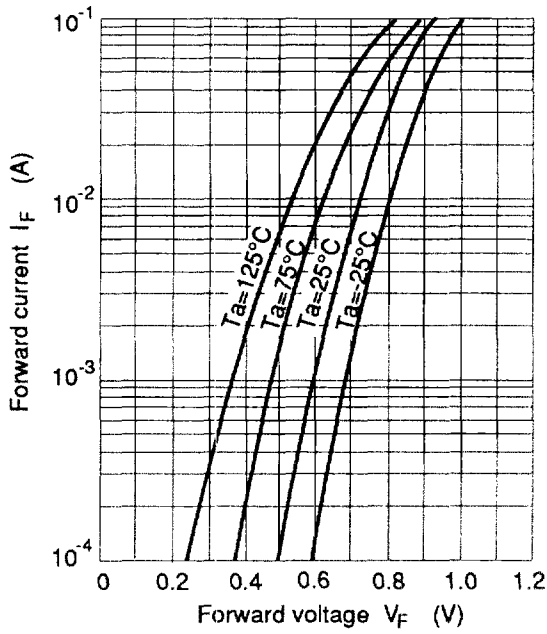


Fig.1 Forward current Vs. Forward voltage

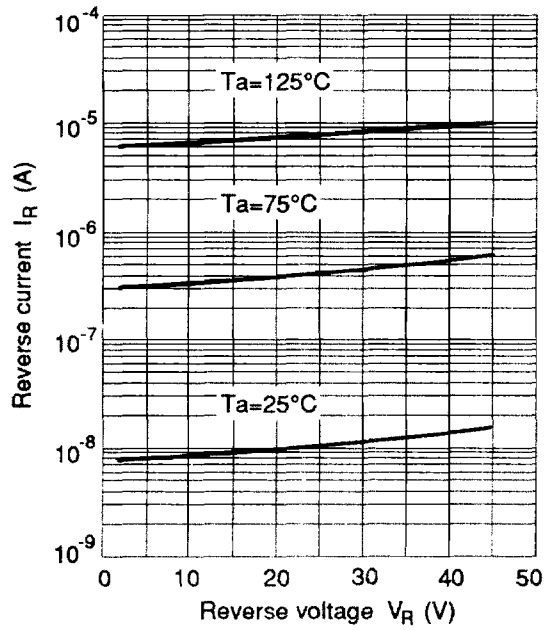


Fig.2 Reverse current Vs. Reverse voltage

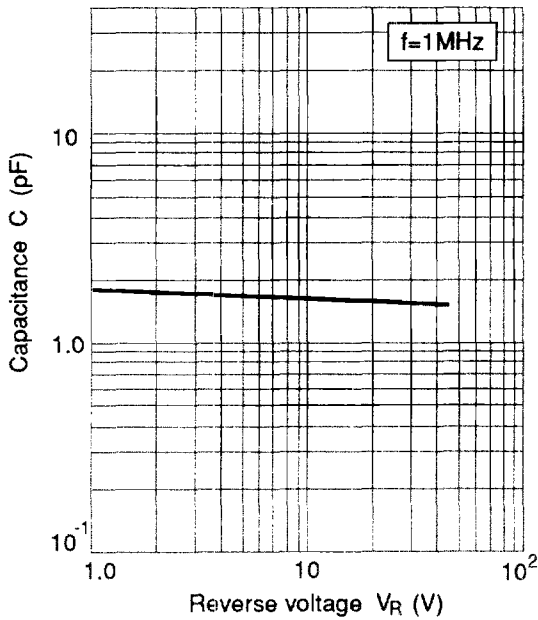


Fig.3 Capacitance Vs. Reverse voltage